Notification about the transfer of the semiconductor business

The semiconductor business of Panasonic Corporation was transferred on September 1, 2020 to Nuvoton Technology Corporation (hereinafter referred to as "Nuvoton"). Accordingly, Panasonic Semiconductor Solutions Co., Ltd. became under the umbrella of the Nuvoton Group, with the new name of Nuvoton Technology Corporation Japan (hereinafter referred to as "NTCJ").

In accordance with this transfer, semiconductor products will be handled as NTCJ-made products after September 1, 2020. However, such products will be continuously sold through Panasonic Corporation.

Publisher of this Document is NTCJ.

If you would find description "Panasonic" or "Panasonic semiconductor solutions", please replace it with NTCJ.

Except below description page
 "Request for your special attention and precautions in using the technical information and semiconductors described in this book"

Nuvoton Technology Corporation Japan

Doc No. TT4-EA-14734

Revision. 2

MOS FET

FC6B22100L

Panasonic

FC6B22100L

Gate resistor installed Dual N-channel MOS FET

For lithium-ion secondary battery protection circuits

■ Features

- Low source-source ON resistance:Rss(on) typ. = 8.2 mΩ(VGS = 4.5 V)
- · CSP package:smallest & thinnest size
- RoHS compliant (EU RoHS / MSL:Level 1 compliant)
- Marking Symbol: 35

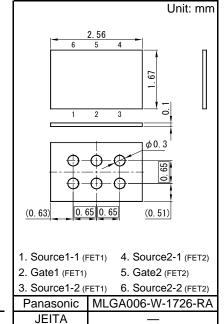
■ Packaging

Embossed type (Thermo-compression sealing): 10 000 pcs / reel (standard)

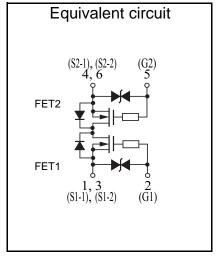
■ Absolute Maximum Ratings Ta = 25 °C

Parameter		Symbol	Rating	Unit	
Source-source Voltage		VSS	24	V	
Gate-source Voltage		VGS	±12	V	
Source Current	DC *1	IS1	6	Α	
	DC *2	IS2	13	Α	
	Pulse *3	ISp	100	Α	
Total Power Dissipation	DC ^{*1}	PD1	0.45	W	
	DC *2	PD2	2.1	W	
Channel Temperature		Tch	150	°C	
Storage Temperature Range		Tstg	-55 to +150	°C	
Thermal resistance (ch-a)	DC ^{*1}	Rth1	278	°C/W	
	DC *2	Rth2	59	°C/W	

- Note *1 Mounted on FR4 board ($25.4~\text{mm} \times 25.4~\text{mm} \times t1.0~\text{mm}$) using the minimum recommended pad size ($36~\text{\mu m}$ Copper).
 - *2 Mounted on Ceramic substrate (70 mm \times 70 mm \times t1.0 mm).
 - *3 $\,$ t = 10 $\mu s,$ Duty Cycle \leq 1 %



Code



MOS FET

FC6B22100L

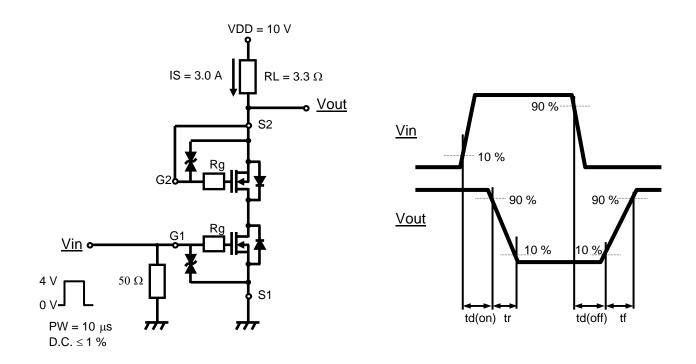
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■ Electrical Characteristics Ta = 25 °C ± 3 °C

Parameter	Symbol	Conditions	Min	Тур	Max	Unit	
Source-source Breakdown Voltage	VSSS	IS = 1 mA, VGS = 0 V	24			V	
Zero Gate Voltage Source Current	ISSS	VSS = 24 V, VGS = 0 V			1.0	μΑ	
Gate-source Leakage Current	IGSS	$VGS = \pm 8 \text{ V}, VSS = 0 \text{ V}$			±10	μА	
		$VGS = \pm 5 V$, $VSS = 0 V$			±1.0	μΑ	
Gate-source Threshold Voltage	Vth	IS = 1.2 mA, VSS = 10 V	0.40	0.90	1.4	V	
Source-source On-state Resistance	RSS(on)1	IS = 3.0 A, VGS = 4.5 V	5.7	8.2	11.2		
	RSS(on)2	IS = 3.0 A, VGS = 3.8 V	5.9	8.7	12.2	mΩ	
	RSS(on)3	IS = 3.0 A, VGS = 3.1 V	6.3	9.7	14.7		
	RSS(on)4	IS = 3.0 A, VGS = 2.5 V	7	12.5	22.5		
Body Diode Forward Voltage	VF(s-s)	IF = 6.0 A, VGS = 0 V		0.8	1.2	V	
Input Capacitance *1	Ciss			3000		pF	
Output Capacitance *1	Coss	VSS = 10 V, VGS = 0 V, f = 1 MHz		250			
Reverse Transfer Capacitance *1	Crss			220			
Turn-on delay Time *1,*2	td(on)	VDD = 10 V, VGS = 0 to 4.0 V		1.1		0	
Rise Time *1,*2	tr	IS = 3.0 A		1.8		μS	
Turn-off delay Time *1,*2	td(off)	VDD = 10 V, VGS = 4.0 to 0 V		6.9		0	
Fall Time *1,*2	tf	IS = 3.0 A		3.6		μS	
Total Gate Charge *1	Qg	VDD = 10 V		27.6			
Gate-source Charge *1	Qgs	VGS = 0 to $4.0 V$,		5.6		nC	
Gate-drain Charge *1	Qgd	IS = 6.0 A		7.5			

Note Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 Measuring methods for transistors.

^{*2} Measurement circuit for Turn-on Delay Time / Rise Time / Turn-off Delay Time / Fall Time



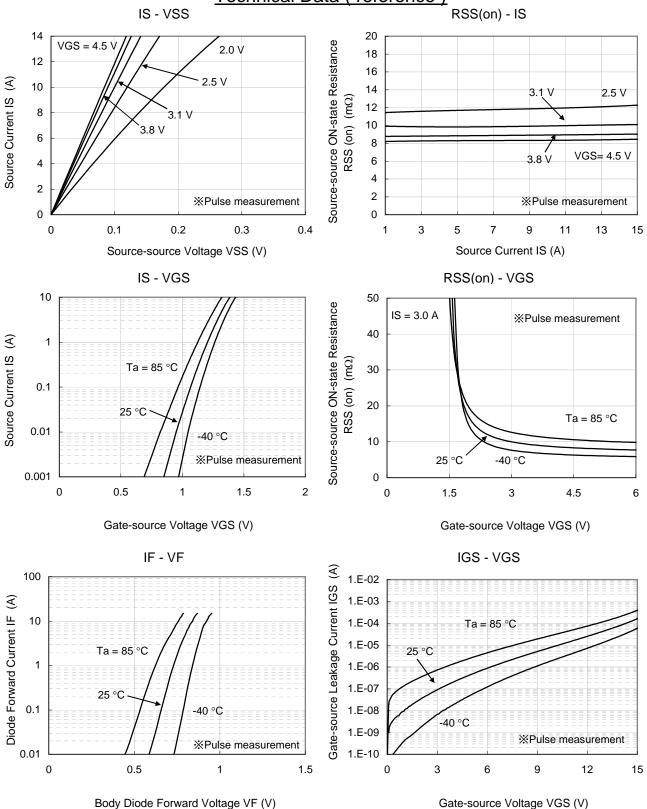
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^{*1} Assured by design

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MOS FET FC6B22100L

Technical Data (reference)

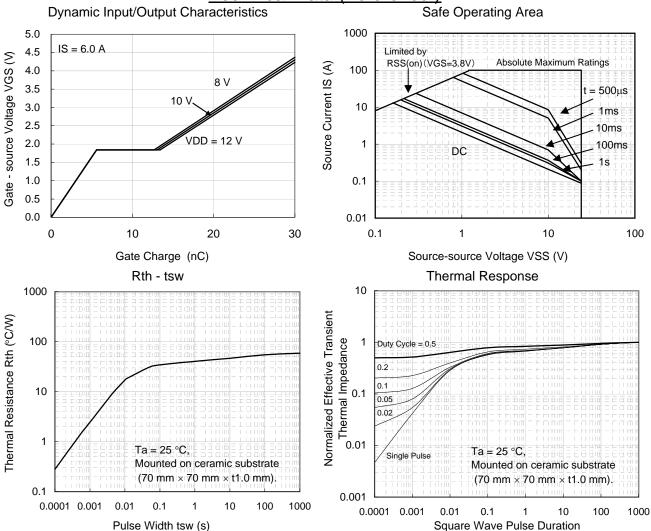


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Revision. 2

MOS FET FC6B22100L

Technical Data (reference)



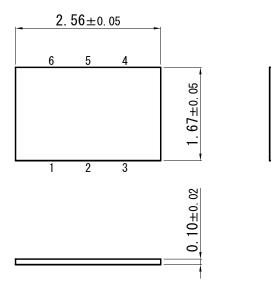
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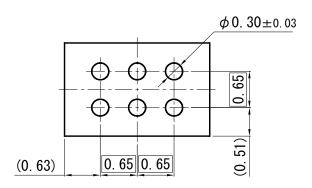
MOS FET

FC6B22100L

MLGA006-W-1726-RA

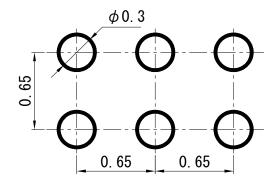
Unit: mm





■ Land Pattern (Reference)

Unit: mm



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